

**UT3443**

Preliminary

Power MOSFET**P-CHANNEL 2.5-V (G-S)
MOSFET**

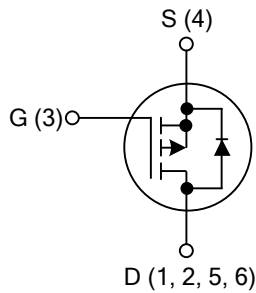
■ DESCRIPTION

The UTC **UT3443** is a P-channel power MOSFET using UTC's advanced trench technology to provide customers with a minimum on-state resistance and extremal low gate charge with a 12V gate rating.

■ FEATURES

* $V_{DS(V)} = -20V$ * $I_D = -4.5A$ * $R_{DS(ON)} < 100m\Omega @ V_{GS} = -2.5V$, $R_{DS(ON)} < 65m\Omega @ V_{GS} = -4.5V$

■ SYMBOL



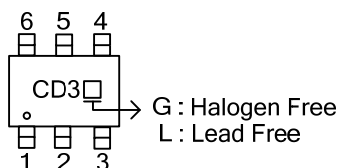
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1, 2, 5, 6	3	4	
UT3443L-AG6-R	UT3443G-AG6-R	SOT-26	D	G	S	Tape Reel

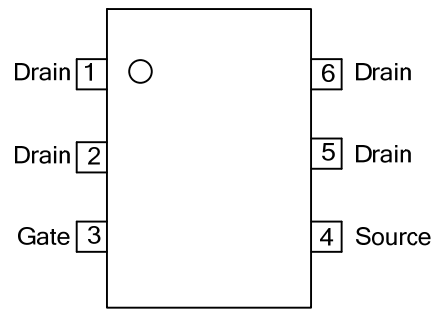
Note: Pin Assignment: G: Gate D: Drain S: Source

UT3443L-AG6-R	(1) Packing Type	(1) R: Tape Reel
	(2) Package Type	(2) AG6: SOT-26
	(3) Lead Free	(3) G: Halogen Free, L: Lead Free

■ MARKING



■ PIN CONFIGURATION



■ ABSOLUTE MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER			SYMBOL	RATINGS	UNIT
Drain-Source Voltage			V_{DSS}	-20	V
Gate-Source Voltage			V_{GSS}	± 12	V
Drain Current	Continuous	$T_A=25^{\circ}\text{C}$	I_{D}	-4.5	A
	$T_J=150^{\circ}\text{C}$ (Note 2)	$T_A=70^{\circ}\text{C}$		-3.6	
	Pulsed		I_{DM}	-20	
Power Dissipation (Note 2)		$T_A=25^{\circ}\text{C}$	P_{D}	1.1	W
Junction Temperature			T_J	+150	$^{\circ}\text{C}$
Storage Temperature			T_{STG}	-55~+150	$^{\circ}\text{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient (Note 1)	θ_{JA}	110	$^{\circ}\text{C/W}$

Note: 1. Surface Mounted on FR4 Board, $t \leq 5$ sec

■ ELECTRICAL CHARACTERISTICS ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Leakage Current		I _{DSS}	V _{DS} =-20V, V _{GS} =0V			-1	μA
			V _{DS} =-20V, V _{GS} =0V, T _C =70°C			-5	
Gate- Source Leakage Current	Forward	I _{GSS}	V _{GS} =+12V, V _{DS} =0V			+100	nA
	Reverse		V _{GS} =-12V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =-250μA	-0.6		-1.4	V
Static Drain-Source On-State Resistance (Note 2)		R _{DS(ON)}	V _{GS} =-4.5V, I _D =-4.5A		0.050	0.065	Ω
			V _{GS} =-2.7V, I _D =-3.8A		0.070	0.090	
			V _{GS} =-2.5V, I _D =-3.7A		0.080	0.100	
SWITCHING PARAMETERS (Note 3)							
Total Gate Charge		Q _G	V _{GS} =-4.5V, V _{DS} =-10V, I _D =-4.5A		7.3	15	nC
Gate to Source Charge		Q _{GS}			2.0		nC
Gate to Drain Charge		Q _{GD}			1.9		nC
Gate Resistance		R _g		3		15	Ω
Turn-ON Delay Time		t _{D(ON)}	V _{DD} =-10V, I _D ≈-1.0A, V _{GEN} =-4.5V, R _L =10Ω, R _G =6Ω		15	50	ns
Rise Time		t _R			32	60	ns
Turn-OFF Delay Time		t _{D(OFF)}			50	100	ns
Fall-Time		t _F			45	80	ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Drain-Source Diode Forward Voltage (Note 2)		V _{SD}	I _S =-1.7A, V _{GS} =0V		-0.8	-1.2	V
Body Diode Reverse Recovery Time		t _{RR}	I _F =-1.7A, di/dt=100A/μs		35	80	ns

Notes: 2. Pulse test; pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.

3. Guaranteed by design, not subject to production testing.

UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.